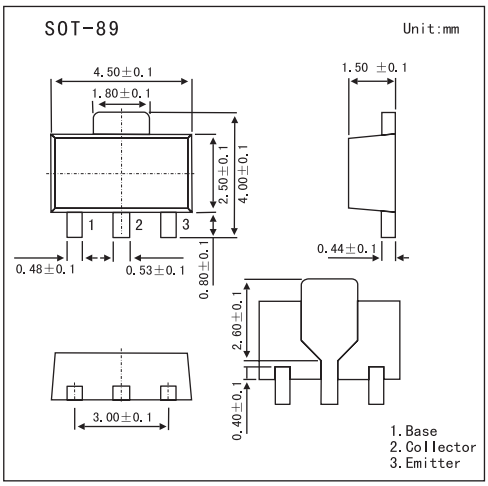
Medium Power Transistor

2SB1188



■ Features

- Low $V_{CE(sat)}$.

  $V_{CE(sat)}$ = -0.5V (Typ.)

  (I_C/I_B = -2A / -0.2A)

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base Voltage	V_{CBO}	-40	V
Collector-emitter Voltage	V_{CEO}	-32	V
Emitter-base Voltage	V_{EBO}	-5	V
Collector current	I_C	-2	A
	I_{CP} *	-3	A
Collector power dissipation	P_C	0.5	W
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW=100ms

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltae	BV_{CBO}	I_C = -50μA	-40			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C = -1mA	-32			V
Emitter-base breakdown voltage	BV_{EBO}	I_E = -50μA	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -20V			-1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -4V			-1	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -2A , I_B = -0.2A		-0.5	-0.8	V
DC current transfer ratio	h_{FE}	V_{CE} = -3V , I_C = -0.5A	82		390	
Transition frequency	f_T	V_{CE} = -5V , I_E = 0.5A , f = 30MHz		100		MHz
Output Capacitance	C_{ob}	V_{CB} = -10V , I_E = 0, f = 1MHz		50		pF

■ h_{FE} Classification

Marking	BC		
Rank	P	Q	R
hFE	82～180	120～270	180～390